

#### **UPS560e3**

# **5 A Schottky Barrier Rectifier**

#### **DESCRIPTION**

This UPS560e3 in the Powermite3® package is a high efficiency Schottky rectifier that is also RoHS compliant offering high current/power capabilities previously found only in much larger packages. They are ideal for SMD applications that operate at high frequencies. In addition to its size advantages, the Powermite3® package includes a full metallic bottom that eliminates the possibility of solder flux entrapment during assembly and a unique locking tab act as an efficient heat path to the heat-sink mounting. Its innovative design makes this device ideal for use with automatic insertion equipment.

IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

# ABSOLUTE MAXIMUM RATINGS AT 25° C (UNLESS OTHERWISE SPECIFIED)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} egin{array}{c} egin{array}$	60	V
RMS Reverse Voltage	V <sub>R (RMS)</sub>	42	V
Average Rectified Output Current	Io	5	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on Rated Load@ T <sub>c</sub> =90 °C	I <sub>FSM</sub>	100	А
Storage Temperature	$T_{STG}$	-55 to +150	°C
Junction Temperature	$T_J$	-55 to +125	°C

#### THERMAL CHARACTERISTICS

Thermal Resistance			
Junction-to-case (bottom)	R <sub>eJC</sub>	3.2	°C/ Watt
Junction to ambient (1)	Raia	65	°C/ Watt

(1) When mounted on FR-4 PC board using 2 oz copper with recommended minimum foot print

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Note: 1 Short duration test pulse used to minimize self – heating effect.

#### **KEY FEATURES**

- Very low thermal resistance package
- RoHS Compliant with e3 suffix part number
- Guard-ring-die construction for transient protection
- Efficient heat path with Integral locking bottom metal tab
- Low forward voltage
- Full metallic bottom eliminates flux entrapment
- Compatible with automatic insertion
- Low profile-maximum height of 1mm

#### APPLICATIONS/BENEFITS

- Switching and Regulating Power Supplies.
- Silicon Schottky (hot carrier) rectifier for minimal reverse voltage recovery
- Elimination of reverse-recovery oscillations to reduce need for EMI filtering
- Charge Pump Circuits
- Reduces reverse recovery loss with low I<sub>RM</sub>
- Small foot print
  190 X 270 mils (1:1 Actual size)
  See mounting pad details on pg 3

#### **MECHANICAL & PACKAGING**

- CASE: Void-free transfer molded thermosetting epoxy compound meeting UL94V-0
- FINISH: Annealed matte-Tin plating over copper and readily solderable per MIL-STD-750 method 2026 (consult factory for Tin-Lead plating)
- POLARITY: See figure (left)
- MARKING: S560•
- WEIGHT: 0.072 gram (approx.)
- Package dimension on last page
- Tape & Reel option: 16 mm tape per Standard EIA-481-B, 5000 on 13" reel

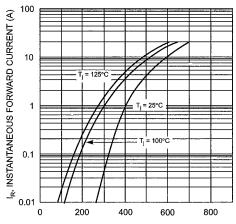


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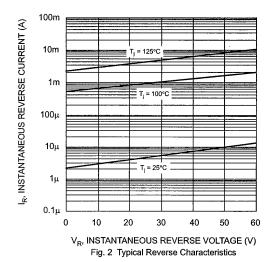
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ELECTRICAL PARAMETERS @ 25°C (unless otherwise specified)								
Parameter	Symbol	Conditions	Min	Тур.	Max	Units		
Forward Voltage (Note 1)	$V_{Fm}$	$I_F = 5 \text{ A}$ , $T_j = 25 \text{ °C}$ $I_F = 5 \text{ A}$ , $T_j = 125 \text{ °C}$ $I_F = 8 \text{ A}$ , $T_j = 25 \text{ °C}$ $I_F = 8 \text{ A}$ , $T_i = 125 \text{ °C}$		0.65 0.56 0.74 0.64	0.69 0.60 0.78 0.68	V		
Reverse Break Down Voltage (Note 1)	$V_{BR}$	I <sub>R</sub> = 0.2 mA	60	0.04	0.00	V		
Reverse Current (Note1)	I <sub>m</sub>	V <sub>R</sub> = 60 V, T <sub>j</sub> = 25°C V <sub>R</sub> = 60 V, T <sub>j</sub> = 125 °C		2 0.6	200 20	μA mA		
Capacitance	C <sub>T</sub>	$V_R = 4 \text{ V}; F = 1 \text{ MH}_Z$		150		pF		

#### GRAPHS



 $V_{\text{F}}$ , INSTANTANEOUS FORWARD VOLTAGE (mV) Fig. 1 Typical Forward Characteristics



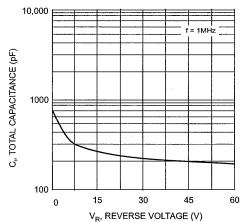
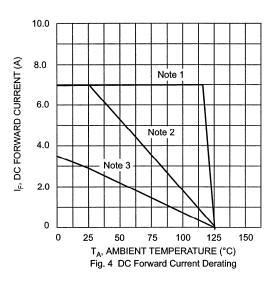


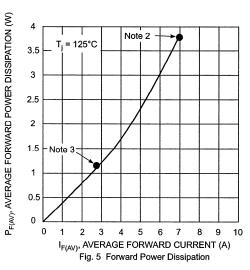
Fig. 3 Typical Capacitance vs. Reverse Voltage



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- NOTE 1:  $T_A = T_C$  at case bottom where  $R_{\theta JC} = 2.5^{\circ}$  C/W and  $R_{\theta CA} = 0^{\circ}$  C/W (infinite heat sink).
- NOTE 2: Device mounted on GETEK substrate, 2" x 2", 2 oz. copper , double-sided , cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0".  $R_{\theta JA}$  in range of 20-35° C/W.
- NOTE 3: Device mounted on FRA-4 substrate, 2" x 2", 2 oz. copper, single-sided, pad layout R<sub>0JA</sub> in range of 65°C/W. See

#### PACKAGE & MOUNTING PAD DIMENSIONS (inches)

